DMA2610F

Silicon PNP epitaxial planar type

For digital circuits

■ Features

- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DRA2143X (Common emitter)

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I_{C}	-100	mA
Total power dissipation	P_{T}	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Package

• Code

Mini5-G3-B

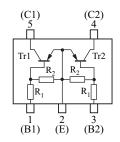
• Pin Name

1: Base (Tr1) 4: Collector (Tr2) 2: Emitter (Common) 5: Collector (Tr1)

3: Base (Tr2)

■ Marking Symbol: R3

■ Internal Connection



Resistance value	R_1	4.7	kΩ
	R_2	10	kΩ

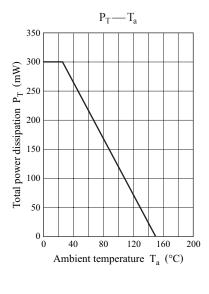
■ Electrical Characteristics $T_a = 25$ °C±3°C

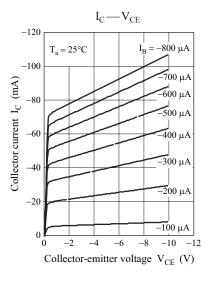
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu{\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\rm CB} = -50 \text{ V}, I_{\rm E} = 0$			-0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{ V}, I_{B} = 0$			-0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-1.0	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	30			_
h _{FE} ratio *	h _{FE} (Small/Large)	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	0.50	0.99		
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	V _{I(on)}	$V_{CE} = -0.2 \text{ V}, I_{C} = -5 \text{ mA}$	-1.7			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = -5 \text{ V}, I_{C} = -100 \mu\text{A}$			-0.6	V
Input resistance	R_1		-30%	4.7	+30%	kΩ
Resistance ratio	R_1/R_2		0.37	0.47	0.57	

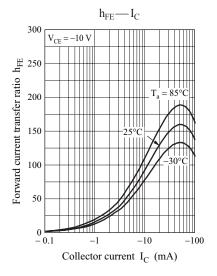
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

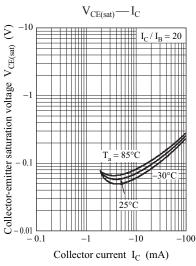
2. *: Ratio between 2 elements

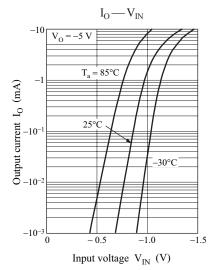
DMA2610F Panasonic

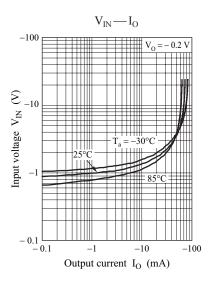








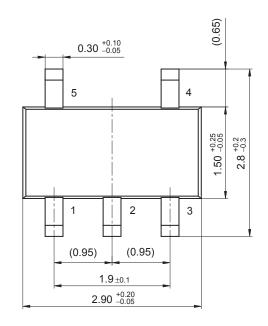


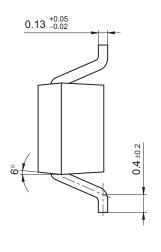


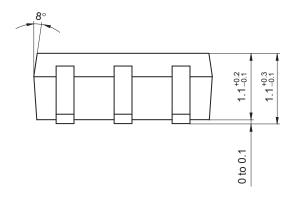
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Panasonic DMA2610F

Mini5-G3-B Unit: mm







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